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[\[Abstract\]](#) [\[PDF Full-Text \(200 KB\)\]](#) **JNL****2 Hot carrier induced degradation in mesa-isolated n-channel SOI MOSFETs operating in a Bi-MOS mode***Ru Huang; Jinyan Wang; Xing Zhang; Yangyuan Wang*

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[\[Abstract\]](#) [\[PDF Full-Text \(292 KB\)\]](#) **CNF****4 Hot-carrier effects and reliable lifetime prediction in deep submicron N- and P-channel SOI MOSFETs***Shing-Hwa Renn; Pelloie, J.-L.; Balestra, F.*

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**5 A thorough investigation of the degradation induced by hot-carrier injection in deep submicron N- and P-channel partially and fully depleted unibond and SIMOX MOSFETs**

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